P3MPB9P0

20V P-Channel MOSFETs

General Description

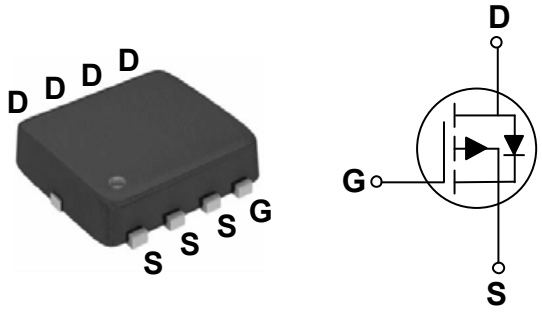
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
-20 V	9 mΩ	-50 A

Features

- $R_{DS(ON)} \leqq 9m\Omega @ V_{GS}$= -4.5V
- Fast switching
- Green Device Available
- Improved dv/dt Capability

PPAK3X3 Pin Configuration



Applications

- Battery Protection
- Load Switch
- Uninterruptible Power Supply

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current - Continuous (T_C=25°C)	-50	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	-100	A
P_D	Power Dissipation (T_C=25°C)	29	W
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		PB9P0	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	75	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	4.2	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D= -250uA	-20	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}= -20V , V_{GS}=0V , T_J=25°C	---	---	-1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±12V , V_{DS}=0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}= -4.5V , I_D= -15A	---	---	9	mΩ
		V_{GS}= -2.5V , I_D= -10A	---	---	11	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D= -250uA	-0.3	---	-1.0	V
gfs	Forward Transconductance	V_{DS}= -5V , I_D= -10A	---	43	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}= -15V , V_{GS}= -4.5V , I_D= -10A	---	63	---	nC
Q_{gs}	Gate-Source Charge		---	9.1	---	
Q_{gd}	Gate-Drain Charge		---	13	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}= -10V , V_{GS}= -4.5V , R_G= 3.3Ω , I_D= -10A	---	15.8	---	nS
T_r	Rise Time		---	76.8	---	
$T_{d(off)}$	Turn-Off Delay Time		---	193	---	
T_f	Fall Time		---	186.4	---	
C_{iss}	Input Capacitance	V_{DS}= -15V , V_{GS}= 0V , F= 1MHz	---	5783	---	pF
C_{oss}	Output Capacitance		---	509	---	
C_{rss}	Reverse Transfer Capacitance		---	431	---	

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G= V_D= 0V , Force Current	---	---	-10.7	A
I_{SM}	Pulsed Source Current		---	---	-60	A
V_{SD}	Diode Forward Voltage	V_{GS}= 0V , I_S= -1A , T_J=25°C	---	---	-1.2	V

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. Essentially independent of operating temperature.

Characteristics Curves

Fig.1 I_D vs. T_C

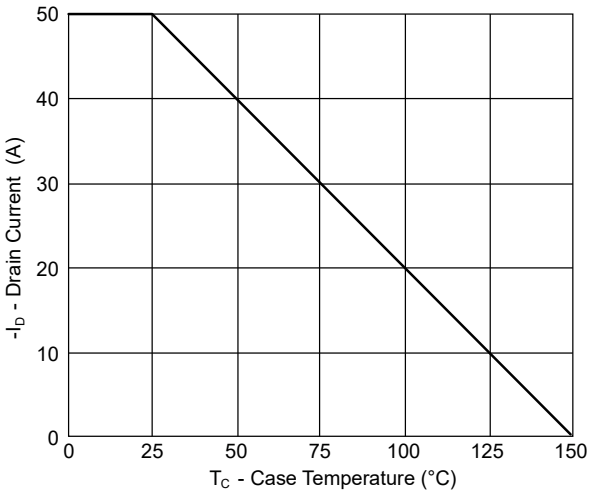


Fig.2 Normalized V_{th} vs. T_J

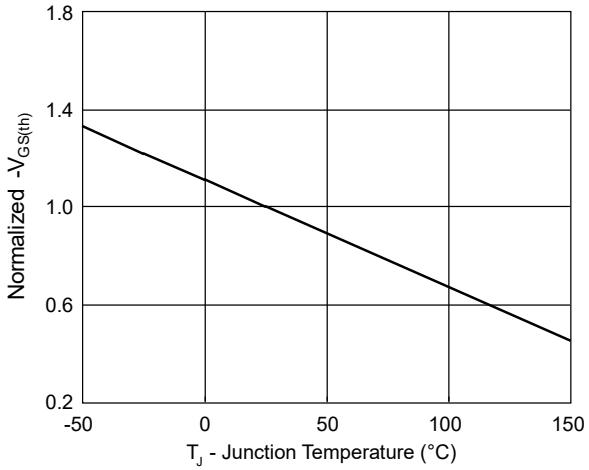


Fig.3 Normalized R_{DSON} vs. T_J

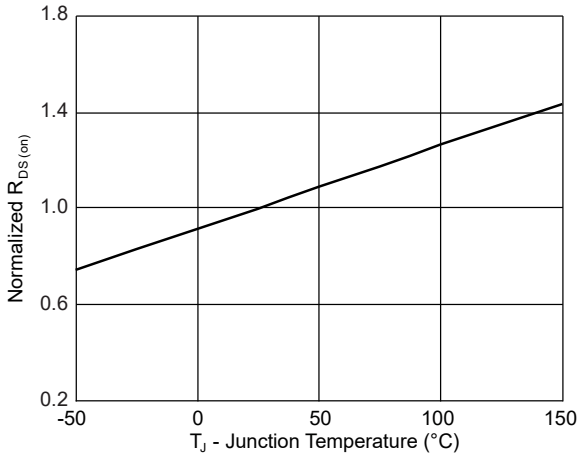


Fig.4 Gate Charge Waveform

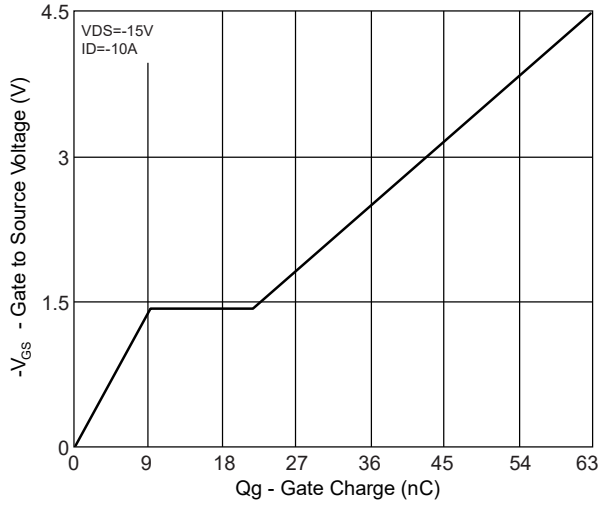


Fig.5 Safe Operation Area

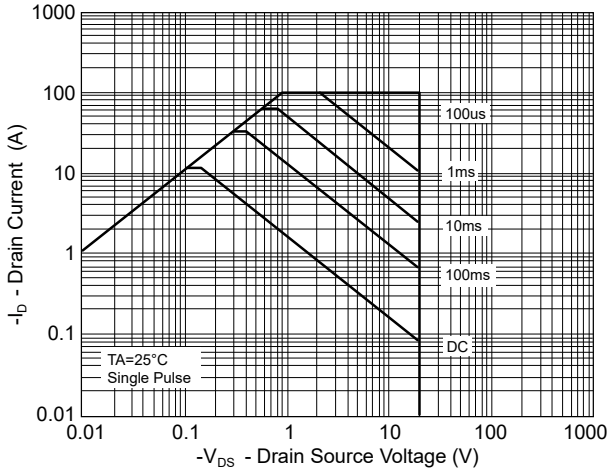
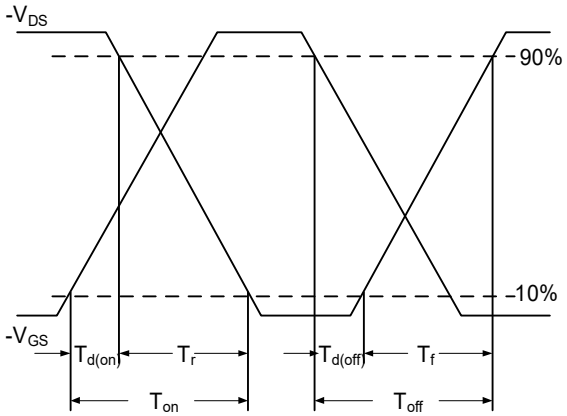
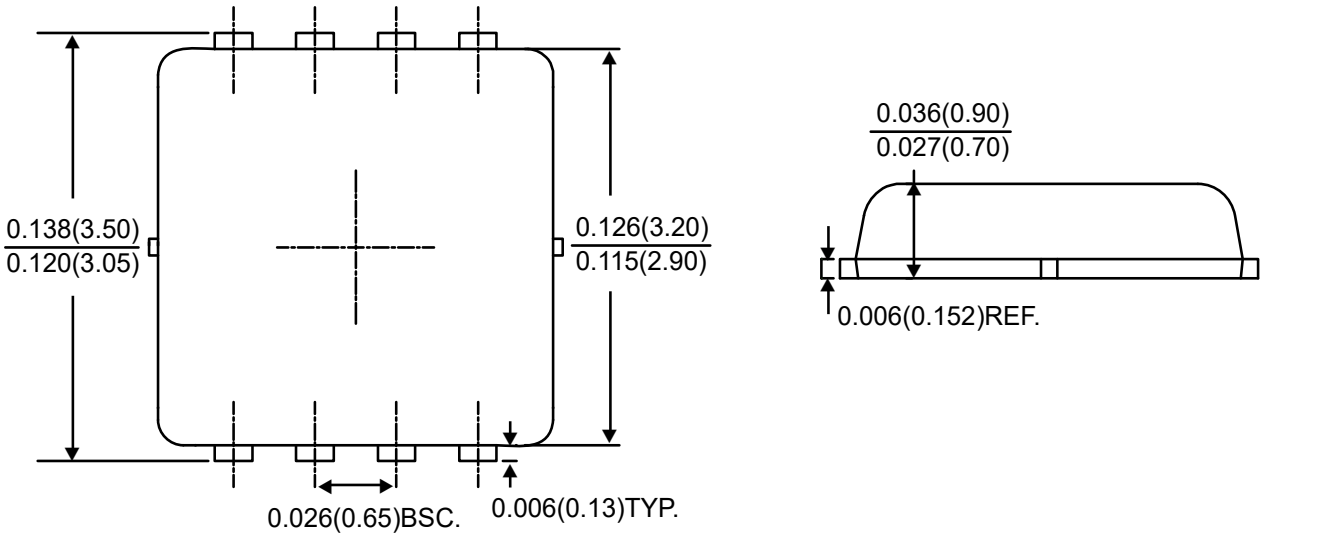


Fig.6 Switching Time Waveform



Package Outline Dimensions



PPAK3X3

Dimensions in inches and (millimeters)

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